

GENERAL DESCRIPTION

The SGM6607 is a monolithic high voltage switching regulator with integrated 1.1A, 40V power MOSFET. The device can be configured in several standard switching-regulator topologies, including boost and SEPIC. The device has a wide input voltage range to support applications with input voltage from multi-cell batteries or regulated 5V, 12V power rails.

The SGM6607 operates at a 1.2MHz switching frequency, allowing the use of low-profile inductors and low-value ceramic input and output capacitors. External loop compensation components give the user flexibility to optimize loop compensation and transient response. The device has built-in protection features, such as cycle-by-cycle over-current limit, output OVP, soft-start and thermal shutdown.

The SGM6607 is available in Green TDFN-2x2-6L and TSOT-23-6 packages and is rated over the -40°C to +85°C temperature range.

FEATURES

- 3V to 20V Input Voltage Range
- High Output Voltage: Up to 38V
- 41V Over-Voltage Protection
- 1.1A Integrated Switch
- 1.2MHz Fixed Switching Frequency
- 12V at 300mA and 24V at 150mA from 5V Input (TYP)
- Up to 93% Efficiency
- Skip-Switching for Light Load
- Built-In Soft-Start Function
- 500kΩ Pull-Down Resistor on EN Pin
- -40°C to +85°C Operating Temperature Range
- Available in Green TDFN-2x2-6L and TSOT-23-6 Packages

APPLICATIONS

- Cell Phones
- Portable Equipment

TYPICAL APPLICATION

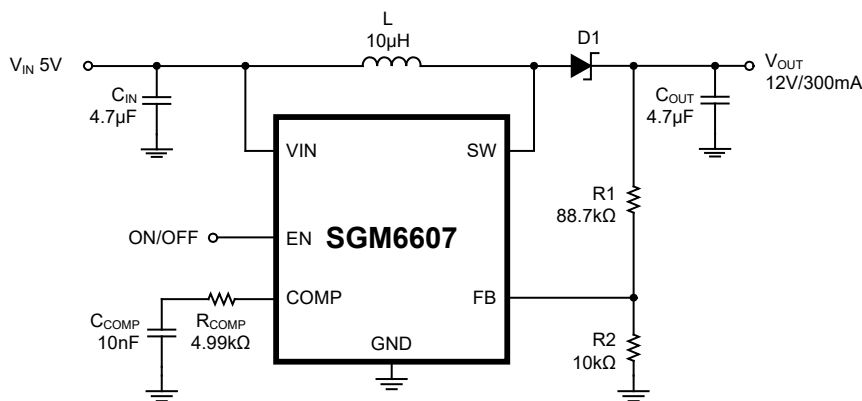


Figure 1. Typical Application Circuit

PACKAGE/ORDERING INFORMATION

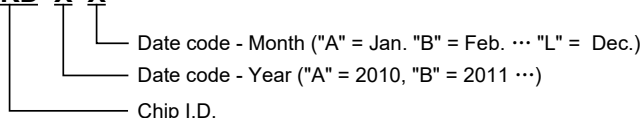
MODEL	PACKAGE DESCRIPTION	SPECIFIED TEMPERATURE RANGE	ORDERING NUMBER	PACKAGE MARKING	PACKING OPTION
SGM6607	TDFN-2x2-6L	-40°C to +85°C	SGM6607YTDI6G/TR	6607 XXXX	Tape and Reel, 3000
	TSOT-23-6	-40°C to +85°C	SGM6607YTN6G/TR	SKDXX	Tape and Reel, 3000

NOTE: XX = Date Code. XXXX = Date Code.

Green (RoHS & HSF): SG Micro Corp defines "Green" to mean Pb-Free (RoHS compatible) and free of halogen substances. If you have additional comments or questions, please contact your SGMICRO representative directly.

MARKING INFORMATION

SKD X X



For example: SKDCD (2012, April)

ABSOLUTE MAXIMUM RATINGS

Supply Voltage on VIN.....	-0.3V to 22V
Voltage on EN.....	-0.3V to 5V
Voltages on FB and COMP.....	-0.3V to 3V
Voltage on SW.....	-0.3V to 40V
Junction Temperature.....	+150°C
Package Thermal Resistance	
TDFN-2x2-6L, θ_{JA}	120°C/W
TSOT-23-6, θ_{JA}	190°C/W
Storage Temperature Range.....	-65°C to +150°C
Lead Temperature (Soldering, 10s).....	+260°C
ESD Susceptibility	
HBM.....	4000V
MM.....	300V

RECOMMENDED OPERATING CONDITIONS

Operating Temperature Range.....	-40°C to +85°C
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OVERSTRESS CAUTION

Stresses beyond those listed may cause permanent damage to the device. Functional operation of the device at these or any other conditions beyond those indicated in the operational section of the specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

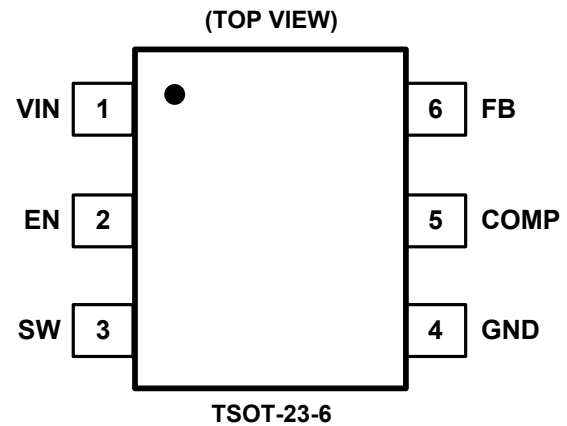
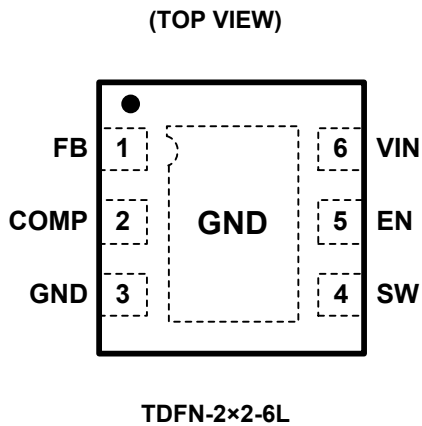
ESD SENSITIVITY CAUTION

This integrated circuit can be damaged by ESD if you don't pay attention to ESD protection. SGMICRO recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

DISCLAIMER

SG Micro Corp reserves the right to make any change in circuit design, specification or other related things if necessary without notice at any time.

PIN CONFIGURATIONS



PIN DESCRIPTION

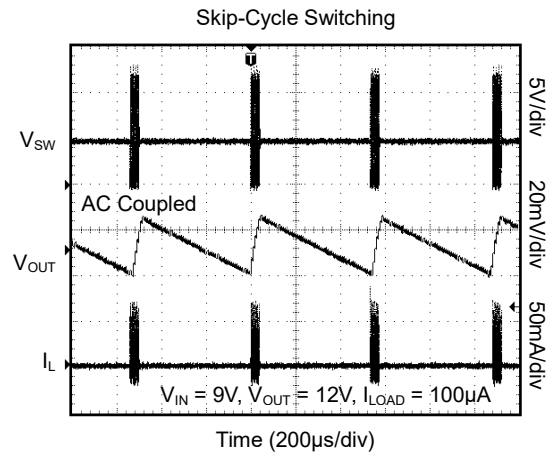
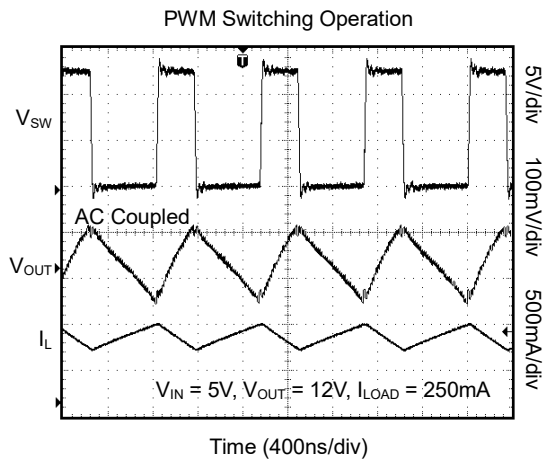
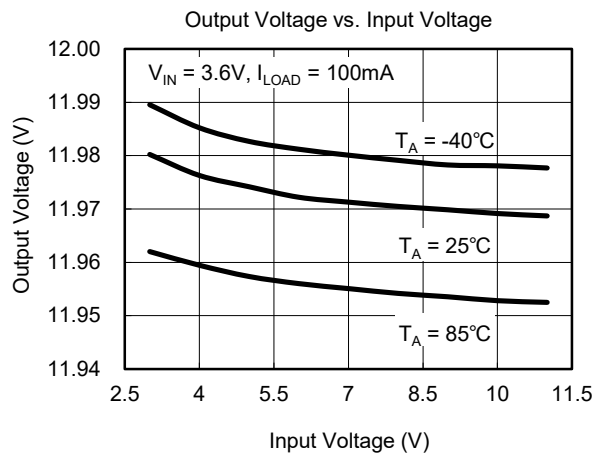
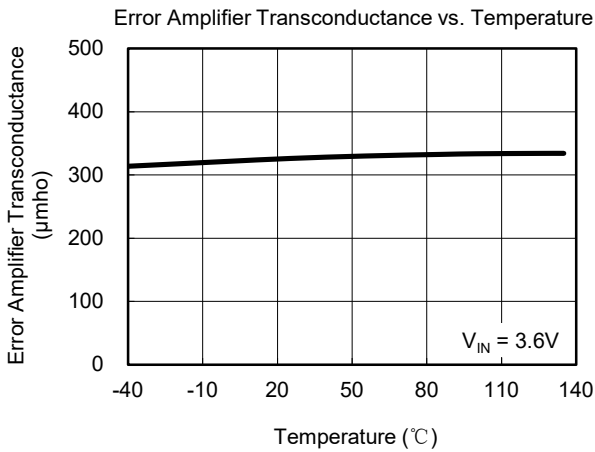
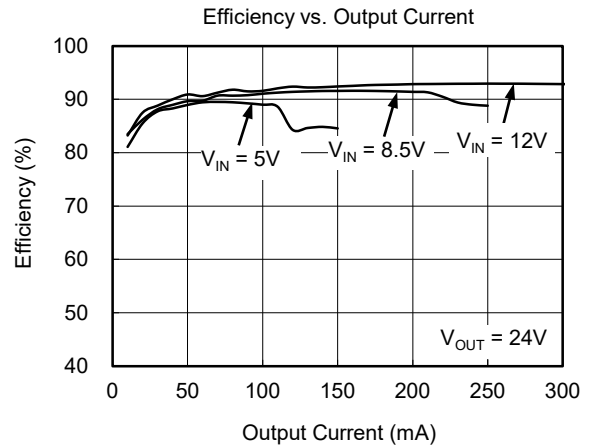
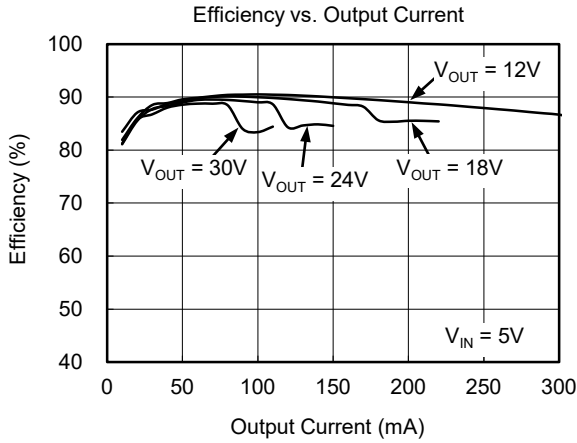
PIN		NAME	I/O	FUNCTION
TDFN-2x2-6L	TSOT-23-6			
6	1	VIN	I	The Input Supply Pin for the IC. Connect VIN to a supply voltage between 3V and 20V.
5	2	EN	I	Enable Pin of the Boost Regulator. Logic low disables the chip. Logic high enables the chip.
4	3	SW	I	Switching Node of the IC. Connect SW to the switched side of the inductor.
3	4	GND	O	Ground.
2	5	COMP	O	Output of the Transconductance Error Amplifier. Connect an external RC network to this pin to compensate the regulator.
1	6	FB	I	Feedback Pin for Current. Connect to the center tap of a resistor divider to program the output voltage.
Thermal Pad	—	GND	—	The thermal pad should be soldered to the analog ground plane to avoid thermal issue. If possible, use thermal vias to connect to ground plane for ideal power dissipation.

ELECTRICAL CHARACTERISTICS(V_{IN} = 3.6V, V_{EN} = V_{IN}, Full = -40°C to +85°C, typical values are at T_A = +25°C, unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS	TEMP	MIN	TYP	MAX	UNITS
SUPPLY CURRENT							
Input Voltage Range	V _{IN}		+25°C	3		20	V
Operating Quiescent Current into VIN	I _Q	Device PWM switching no load	+25°C		400	600	μA
Shutdown Current	I _{SHDN}	V _{EN} = GND, V _{IN} = 4.2V	+25°C			1	μA
Under-Voltage Lockout Threshold	UVLO	V _{IN} falling	+25°C		2.2	2.5	V
Under-Voltage Lockout Hysteresis	V _{HYS}		+25°C		70		mV
ENABLE AND REFERENCE CONTROL							
EN Logic High Voltage	V _{IH}	V _{IN} = 3V to 20V	Full	1.5			V
EN Logic Low Voltage	V _{IL}	V _{IN} = 3V to 20V	Full			0.4	V
EN Pull-Down Resistor	R _{EN}		+25°C	300	500	700	kΩ
VOLTAGE AND CURRENT CONTROL							
Voltage Feedback Regulation Voltage	V _{REF}		Full	1.186	1.211	1.236	V
Voltage Feedback Input Bias Current	I _{FB}	V _{FB} = 1.3V	Full			200	nA
Oscillator Frequency	f _{OSC}		Full	0.96	1.2	1.44	MHz
Maximum Duty Cycle	D	V _{FB} = 1.1V	+25°C	90	94		%
Minimum ON Pulse Width	t _{MIN_ON}		+25°C		80		ns
COMP Pin Sink Current	I _{SINK}		+25°C		55		μA
COMP Pin Source Current	I _{SOURCE}		+25°C		55		μA
Error Amplifier Transconductance	G _{EA}		Full	220	300	440	μmho
POWER SWITCH							
N-Channel MOSFET On-Resistance	R _{DS(ON)}	V _{IN} = 3.6V	+25°C		0.36	0.55	Ω
		V _{IN} = 3.0V	+25°C			0.6	
N-Channel Leakage Current	I _{LN_NFET}	V _{SW} = 35V, V _{EN} = 0V	+25°C			1	μA
OC AND SS							
N-Channel MOSFET Current Limit	I _{LIM}		+25°C	0.8	1.1	1.3	A
V _{REF} Ramp Up Time	t _r		+25°C		2		ms
THERMAL SHUTDOWN							
Thermal Shutdown Threshold	T _{SHDN}				150		°C
Thermal Shutdown Threshold Hysteresis	T _{HYS}				15		°C

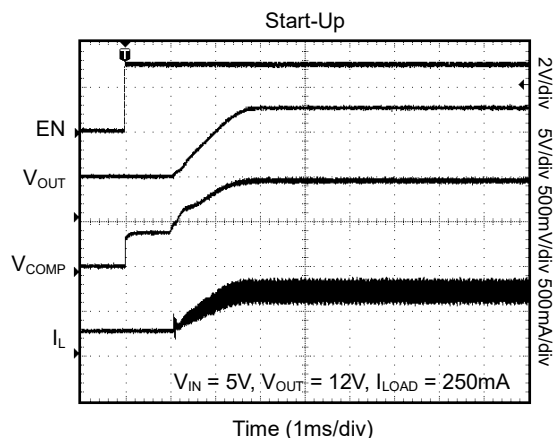
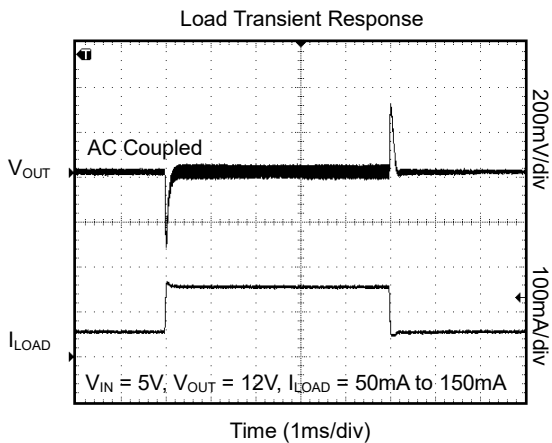
TYPICAL PERFORMANCE CHARACTERISTICS

$T_A = +25^\circ\text{C}$, $L = 10\mu\text{H}$, $D1 = \text{ONsemi MBR0540T1}$, unless otherwise noted.



TYPICAL PERFORMANCE CHARACTERISTICS (continued)

T_A = +25°C, L = 10µH, D1 = ONsemi MBR0540T1, unless otherwise noted.



TYPICAL APPLICATION CIRCUITS

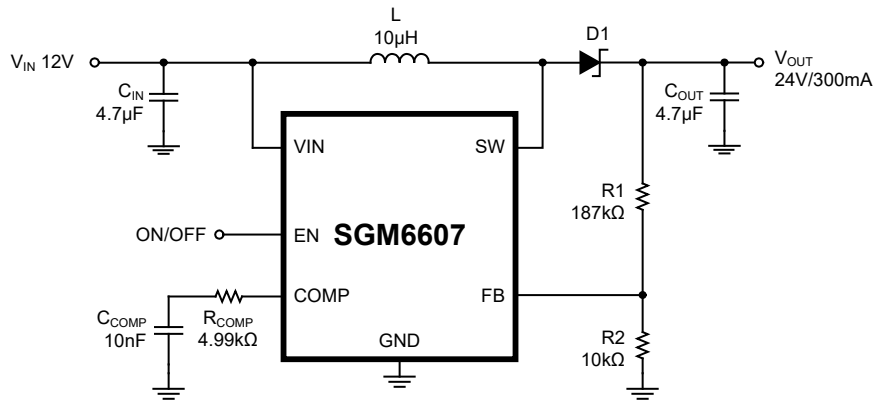


Figure 2. 12V to 24V DC/DC Power Conversion

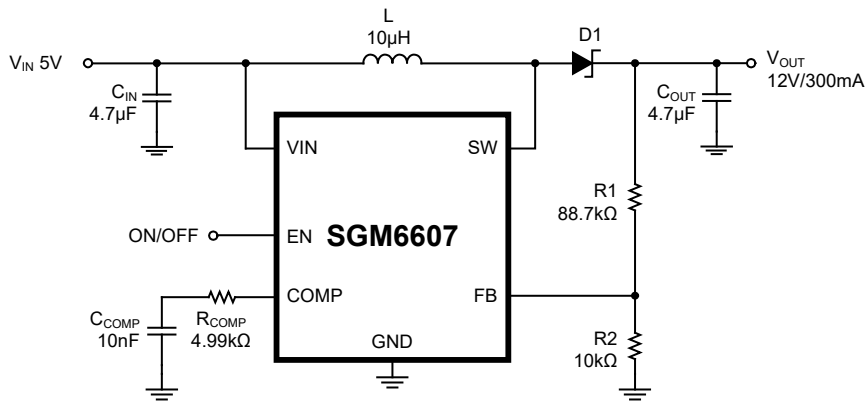


Figure 3. 5V to 12V DC/DC Power Conversion

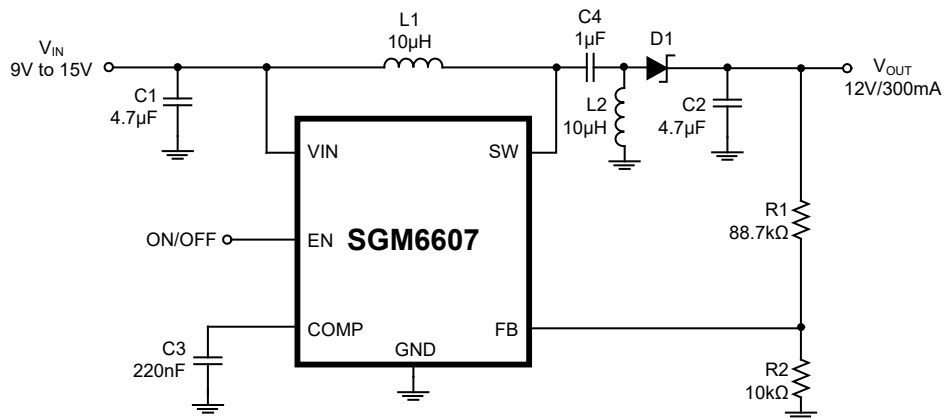


Figure 4. 12V SEPIC (Buck-Boost) Converter

FUNCTIONAL BLOCK DIAGRAM

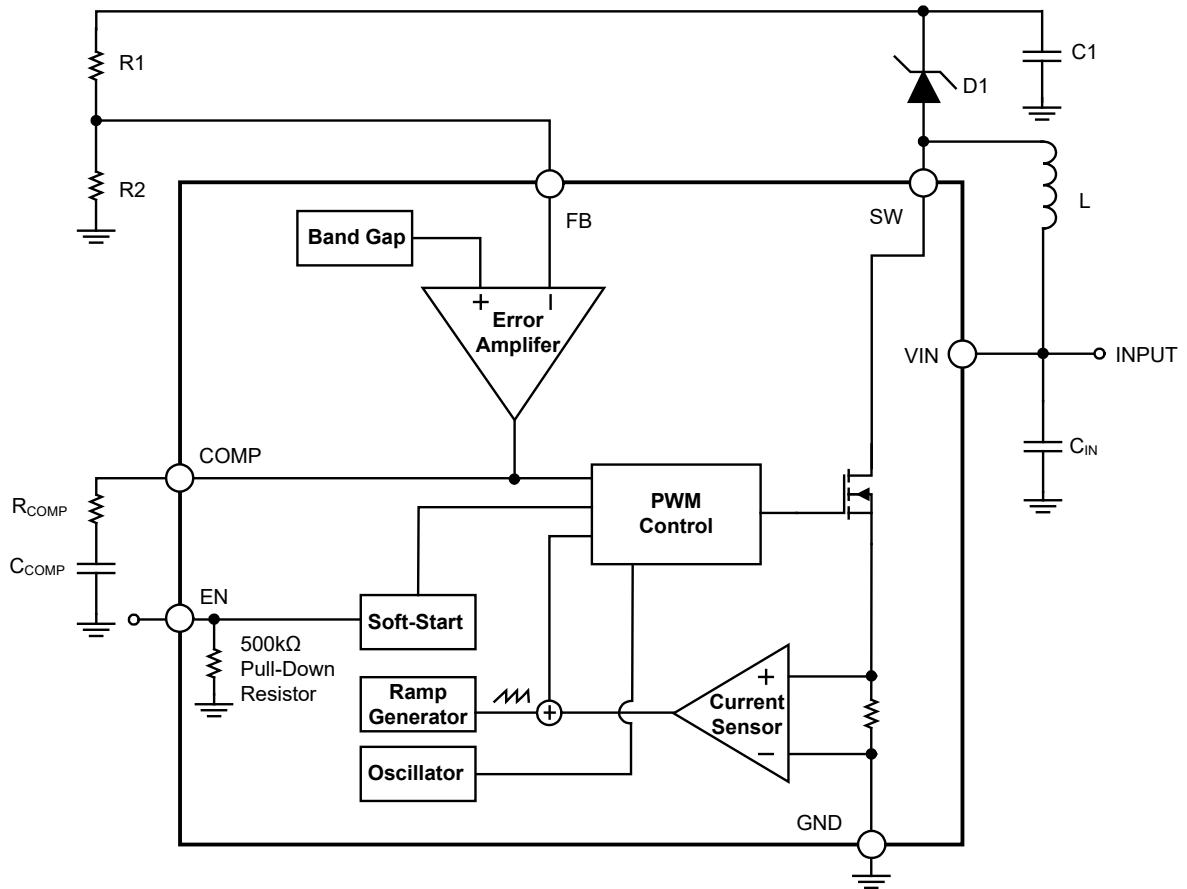


Figure 5. Block Diagram

DETAILED DESCRIPTION

Operation

The SGM6607 integrates a 40V low-side FET for providing output voltages up to 38V. The device regulates the output with current mode PWM (pulse width modulation) control. The switching frequency of the PWM is fixed at 1.2MHz (TYP). The PWM control circuitry turns on the switch at the beginning of each switching cycle. The input voltage is applied across the inductor and stores the energy as the inductor current ramps up. During this portion of the switching cycle, the load current is provided by the output capacitor. When the inductor current rises to the threshold set by the error amplifier output, the power switch turns off and the external Schottky diode is forward biased. The inductor transfers stored energy to replenish the output capacitor and supply the load current. This operation repeats each switching cycle. As shown in the block diagram, the duty cycle of the converter is determined by the PWM control comparator which compares the error amplifier output and the current signal.

A ramp signal from the oscillator is added to the current ramp. This slope compensation ramp is necessary to avoid sub-harmonic oscillations that are intrinsic to current mode control at duty cycles higher than 40%. The feedback loop regulates the FB pin to a reference voltage through an error amplifier. The output of the error amplifier must be connected to the COMP pin. An external RC compensation network must be connected to the COMP pin to optimize the feedback loop for stability and transient response.

Soft-Start

Soft-start circuitry is integrated into the IC to avoid a high inrush current during start-up. After being enabled by a logic high signal on the EN pin, the FB pin reference voltage ramps up to 1.211V in about 2ms. This ensures that the output voltage rises slowly to reduce inrush current.

Over-Current Protection

SGM6607 has a cycle-by-cycle over-current limit feature that turns off the power switch once the inductor current reaches the over-current limit. The PWM circuitry resets itself at the beginning of the next switch cycle. During an over-current event, this results in a decrease of output voltage with respect to load. The current limit threshold as well as input voltage, output voltage, switching frequency and inductor value determine the maximum available output current. Larger inductance values typically increases the

current output capability because of the reduced current ripple. See the Application Information section for the output current calculation.

Under-Voltage Lockout (UVLO)

An under-voltage lockout prevents miss-operation of the device at input voltages below typical 2.2V. When the input voltage is below the under-voltage threshold, the device remains off and the internal switch FET is turned off. The under-voltage lockout threshold is set below minimum operating voltage of 3V to avoid any transient V_{IN} dip triggering the UVLO and causing the device to reset. For input voltages between UVLO threshold and 3V, the device attempts operation, but the performance in specification is not guaranteed.

Over-Voltage Protection (OVP)

Over-voltage protection circuitry prevents IC damage as the result of output resistor divider disconnection. The SGM6607 monitors the voltage at the SW pin during each switching cycle. The circuitry turns off the switch FET and shuts down the IC when the following condition persists for 8 switching clock cycles: the SW voltage exceeds the V_{OVP} threshold. As a result, the output voltage falls to the level of the input supply. The device remains in shutdown mode until it is enabled by toggling the EN pin logic or its power input falls below UVLO. The V_{OVP} threshold of SGM6607 is set at 41V.

It might cause false over-voltage protection if the load voltage stays high when the device is enabled while the V_{IN} is close to UVLO, in which its internal reference for the OVP comparator ramps more slowly and stays too low after an OVP blanking time of around 100 μ s. If the false protection happens, the SGM6607 stops. Enable this device when $V_{IN} > 3V$ or after the load voltage discharges to avoid false protection.

Thermal Shutdown

An internal thermal shutdown turns off the device when the typical junction temperature of +150°C is exceeded. The IC restarts when the junction temperature drops by 15°C.

Enable and Shutdown

The SGM6607 enters shutdown when the EN pin voltage is less than 0.4V. In shutdown, the input supply current for the device is less than 1 μ A (MAX). The EN pin has an internal 500k Ω (TYP) pull-down resistor to disable the device when the pin is left unconnected.

APPLICATION INFORMATION

Program Output Voltage

To program the output voltage, select the values of R1 and R2 (see Figure 6) according to Equation 1.

$$V_{OUT} = 1.211V \times \left(\frac{R1}{R2} + 1 \right)$$

$$R1 = R2 \times \left(\frac{V_{OUT}}{1.211V} - 1 \right) \quad (1)$$

Considering the leakage current through the resistor divider and noise decoupling to FB pin, an optimum value for R2 is around 10kΩ. The output voltage tolerance depends on the accuracy of the reference voltage and the tolerance of R1 and R2.

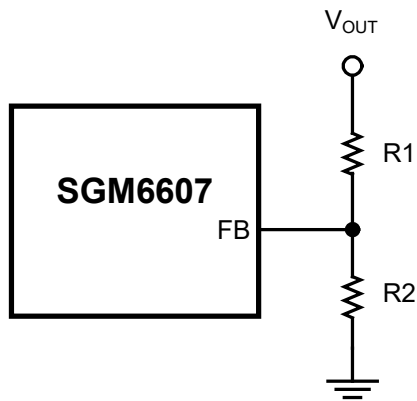


Figure 6. Program Output Voltage

Maximum Output Current

The over-current limit in a boost converter limits the maximum input current, and thus the maximum input power for a given input voltage. The maximum output power is less than the maximum input power due to power conversion losses. Therefore, the current-limit setting, input voltage, output voltage and efficiency can all affect the maximum output current. The current limit clamps the peak inductor current; therefore, the ripple must be subtracted to derive the maximum DC current. The ripple current is a function of the switching frequency, inductor value and duty cycle. The following equations take into account of all the above factors for maximum output current calculation.

$$I_P = \frac{1}{L \times f_S \times \left(\frac{1}{V_{OUT} + V_F - V_{IN}} + \frac{1}{V_{IN}} \right)} \quad (2)$$

where:

I_P = Inductor peak to peak ripple current

L = Inductor value

V_F = Schottky diode forward voltage

f_S = Switching frequency

V_{OUT} = Output voltage

$$I_{OUT_MAX} = \frac{V_{IN} \times \left(I_{LIM} - \frac{I_P}{2} \right) \times \eta}{V_{OUT}} \quad (3)$$

where:

I_{OUT_MAX} = Maximum output current of the boost converter

I_{LIM} = Over-current limit

η = Efficiency

For instance, when V_{IN} is 5V, V_{OUT} is 12V, the inductor is 10μH, the Schottky forward voltage is 0.2V; and then the maximum output current is 300mA in a typical operation.

Switch Duty Cycle

The maximum switch duty cycle (D) of the SGM6607 is 94% (TYP). The duty cycle of a boost converter under continuous conduction mode (CCM) is given by:

$$D = \frac{V_{OUT} - V_{IN}}{V_{OUT}} \quad (4)$$

For a 5V to 12V application, the duty cycle is 58.3%, and for a 5V to 24V application, the duty cycle is 79.2%. The duty cycle must be lower than the maximum specification of 90% in the application; otherwise, the output voltage can not be regulated.

Once the PWM switch is turned on, the SGM6607 has minimum ON pulse width. This sets the limit of the minimum duty cycle. When operating at low duty cycles, the SGM6607 enters pulse-skipping mode. In this mode, the device turns the power switch off for several switching cycles to prevent the output voltage from rising above regulation. This operation typically occurs in light load condition when the PWM operates in discontinuous mode.

APPLICATION INFORMATION (continued)

Inductor Selection

The selection of the inductor affects steady state operation as well as transient behavior and loop stability. These factors make it the most important component in power regulator design. There are three important inductor specifications, inductor value, DC resistance (DCR) and saturation current. Considering inductor value alone is not enough.

The inductance value of the inductor determines its ripple current. It is recommended that the peak-to-peak ripple current given by Equation 2 be set to 30% - 40% of the DC current. Also, the inductance values should not be beyond the range of 6.8μH to 22μH. It is a good compromise of power losses and inductor size. Inductor DC current can be calculated as

$$I_{IN_DC} = \frac{V_{OUT} \times I_{OUT}}{V_{IN} \times \eta} \quad (5)$$

Inductor values can have ±20% tolerance with no current bias. When the inductor current approaches saturation level, its inductance can decrease 20% to 35% from the 0A value depending on how the inductor vendor defines saturation current. Using an inductor with a smaller inductance value forces discontinuous PWM where the inductor current ramps down to zero before the end of each switching cycle. This reduces the boost converter's maximum output current, causes large input voltage ripple and reduces efficiency. In general, inductors with large inductance and low DCR values provide much more output current and higher conversion efficiency. Small inductance value can give better the load transient response. For these reasons, a 6.8μH to 22μH inductance value range is recommended.

SGM6607 has built-in slope compensation to avoid sub-harmonic oscillation associated with current mode control. If the inductor value is lower than 6.8μH, the slope compensation may not be adequate, and the loop can become unstable. Therefore, customers need to verify the inductor in their application if it is different from the recommended values.

Compensation Capacitor Selection

The SGM6607 has an external compensation, COMP pin, which allows the loop response to be optimized for each application. The COMP pin is the output of the internal error amplifier. An external resistor R_{COMP} and ceramic capacitor C_{COMP} are connected to COMP pin to provide a pole and a zero. This pole and zero, along with the inherent pole of a current mode control boost converter, determine the close loop frequency response. This is important to a converter stability and transient response.

The following equations summarize the poles, zeros and DC gain in SGM6607, as shown in the Functional Block Diagram. They include the dominant pole (f_{P1}), the output pole (f_{P2}) of a boost converter, the right-half-plane zero (f_{RHPZ}) of a boost converter, the zero (f_z) generated by R_{COMP} and C_{COMP} and the DC gain (A).

$$f_{P1} = \frac{1}{2\pi \times 140M\Omega \times C_{COMP}} \quad (6)$$

$$f_{P2} = \frac{2}{2\pi \times R_{OUT} \times C_{OUT}} \quad (7)$$

$$f_{RHPZ} = \frac{R_{OUT}}{2\pi \times L} \times \left(\frac{V_{IN}}{V_{OUT}} \right)^2 \quad (8)$$

$$f_z = \frac{1}{2\pi \times R_{COMP} \times C_{COMP}} \quad (9)$$

$$A = \frac{1.211V}{V_{OUT}} \times G_{EA} \times 140M\Omega \times \frac{V_{IN}}{V_{OUT} \times R_{SENSE}} \times R_{OUT} \times \frac{1}{2} \quad (10)$$

where R_{OUT} is the load resistance, G_{EA} is the error amplifier transconductance located in the electrical characteristics table, R_{SENSE} (200mΩ) is a sense resistor in the current control loop. These equations help generate a simple bode plot for SGM6607 loop analysis.

APPLICATION INFORMATION (continued)

Increasing R_{COMP} or reducing C_{COMP} increases the close loop bandwidth which improves the transient response. Adjusting R_{COMP} and C_{COMP} in opposite directions increase the phase, and help loop stability. For many of the applications, the recommended value of 4.99k Ω and 10nF makes an ideal compromise between transient response and loop stability. To optimize the compensation, use C_{COMP} in the range of 1nF to 22nF, and R_{COMP} of 4.99k Ω .

Schottky Diode Selection

The high switching frequency of the SGM6607 demands a high-speed rectification for optimum efficiency. Ensure that the average and peak current rating of the diode exceeds the average output current and peak inductor current. In addition, the diode's reverse breakdown voltage must exceed the switch FET rating voltage of 40V. However, Schottky diodes with lower rated voltages can be used for lower output voltages to save the solution size and cost. For example, a converter providing a 12V output with 20V diode is a good choice.

Input and Output Capacitor Selection

The output capacitor is mainly selected to meet the requirements for the output ripple and loop stability. The ripple voltage is related to the capacitor's capacitance and its equivalent series resistance (ESR). Assuming a capacitor with zero ESR, the minimum capacitance needed for a given ripple can be calculated using Equation 11.

$$C_{OUT} = \frac{(V_{OUT} - V_{IN}) \times I_{OUT}}{V_{OUT} \times f_s \times V_{RIPPLE}} \quad (11)$$

where, V_{RIPPLE} = peak-to-peak output ripple. The additional output ripple component caused by ESR is calculated using:

$$V_{RIPPLE_ESR} = I_{OUT} \times R_{ESR}$$

Due to its low ESR, V_{RIPPLE_ESR} can be neglected for ceramic capacitors, but must be considered if tantalum or electrolytic capacitors are used.

Care must be taken when evaluating a ceramic capacitor's de-rating under DC bias, aging and AC signal. For example, larger form factor capacitors (in 1206 size) have a resonant frequency in the range of the switching frequency. So, the effective capacitance is significantly lower. The DC bias can also significantly reduce capacitance. Ceramic capacitors can lose as much as 50% of its capacitance at its rated voltage. Therefore, choose a ceramic capacitor with a voltage rating at least 1.5 \times its expected DC bias voltage.

The capacitor in the range of 1 μ F to 4.7 μ F is recommended for input side. The output typically requires a capacitor in the range of 1 μ F to 10 μ F. The output capacitor affects the loop stability of the boost regulator. If the output capacitor is below the range, the boost regulator can potentially become unstable.

Thermal Considerations

The maximum IC junction temperature should be restricted to +150 $^{\circ}$ C under normal operating conditions. This restriction limits the power dissipation of the SGM6607. Calculate the maximum allowable dissipation, $P_{D(MAX)}$, and keep the actual dissipation less than or equal to $P_{D(MAX)}$. The maximum-power-dissipation limit is determined using Equation 12:

$$P_{D(MAX)} = \frac{150^{\circ}\text{C} - T_A}{\theta_{JA}} \quad (12)$$

where, T_A is the maximum ambient temperature for the application. θ_{JA} is the package thermal resistance.

The SGM6607 comes in TDFN and TSOT packages. Compared with the TSOT package, the TDFN package has better heat dissipation. This package includes a thermal pad that improves the thermal capabilities of the package. The θ_{JA} of the TDFN package greatly depends on the PCB layout and thermal pad connection. The thermal pad must be soldered to the analog ground on the PCB. Using thermal vias underneath the thermal pad as illustrated in the layout example.

REVISION HISTORY

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

FEBRUARY 2018 – REV.A to REV.A.1

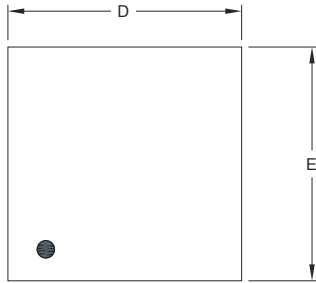
Updated Package Thermal Resistance of TDFN-2x2-6L	2
Updated Over-Voltage Protection (OVP) section	9

Changes from Original (FEBRUARY 2014) to REV.A

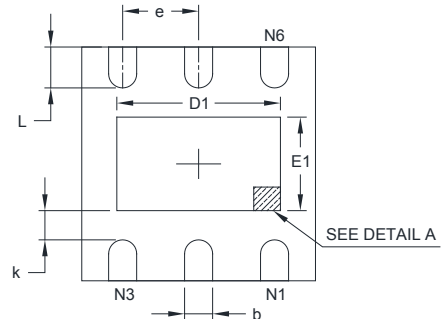
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PACKAGE OUTLINE DIMENSIONS

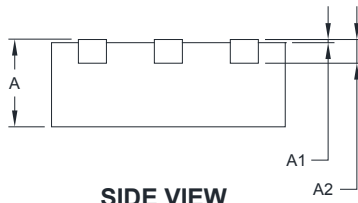
TDFN-2x2-6L



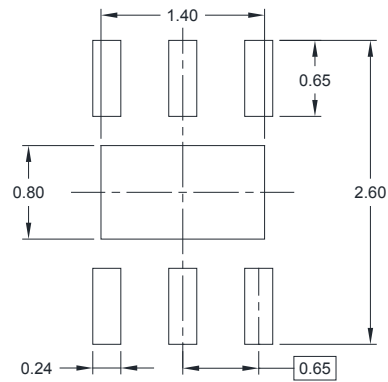
TOP VIEW



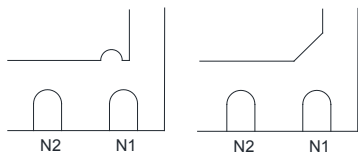
BOTTOM VIEW



SIDE VIEW



RECOMMENDED LAND PATTERN (Unit: mm)



DETAIL A

Pin #1 ID and Tie Bar Mark Options

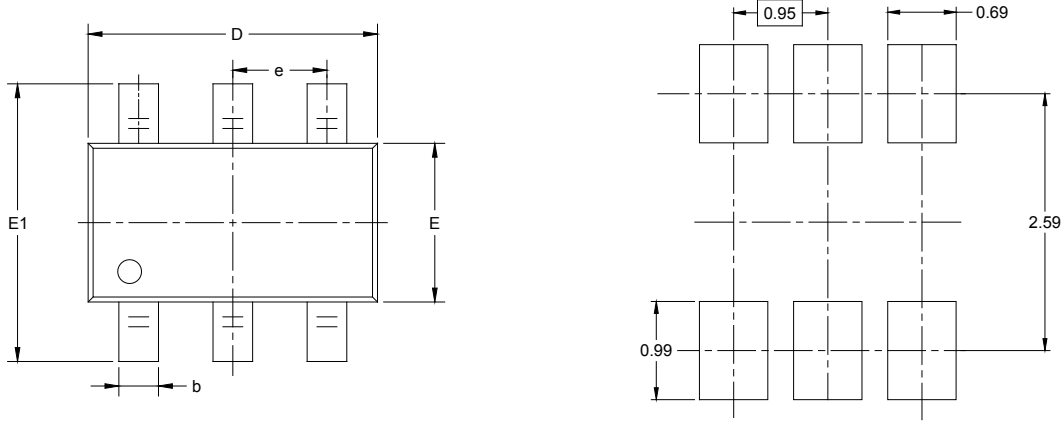
NOTE: The configuration of the Pin #1 identifier is optional, but must be located within the zone indicated.

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A2	0.203 REF		0.008 REF	
D	1.900	2.100	0.075	0.083
D1	1.100	1.450	0.043	0.057
E	1.900	2.100	0.075	0.083
E1	0.600	0.850	0.024	0.034
k	0.200 MIN		0.008 MIN	
b	0.180	0.300	0.007	0.012
e	0.650 TYP		0.026 TYP	
L	0.250	0.450	0.010	0.018

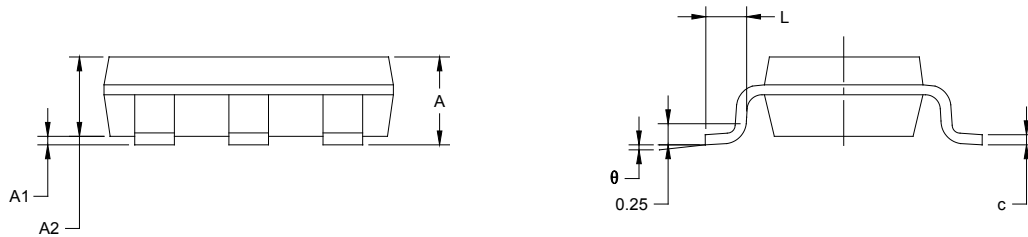
PACKAGE INFORMATION

PACKAGE OUTLINE DIMENSIONS

TSOT-23-6



RECOMMENDED LAND PATTERN (Unit: mm)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A		1.000		0.043
A1	0.000	0.100	0.000	0.004
A2	0.700	0.900	0.028	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.200	0.003	0.008
D	2.850	2.950	0.112	0.116
E	1.550	1.650	0.061	0.065
E1	2.650	2.950	0.104	0.116
e	0.950 BSC		0.037 BSC	
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

PACKAGE INFORMATION

TAPE AND REEL INFORMATION

REEL DIMENSIONS



TAPE DIMENSIONS



NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF TAPE AND REEL

Package Type	Reel Diameter	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
TDFN-2×2-6L	7"	9.5	2.30	2.30	1.10	4.0	4.0	2.0	8.0	Q1
TSOT-23-6	7"	9.5	3.20	3.10	1.10	4.0	4.0	2.0	8.0	Q3

DD0001

PACKAGE INFORMATION

CARTON BOX DIMENSIONS



NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF CARTON BOX

Reel Type	Length (mm)	Width (mm)	Height (mm)	Pizza/Carton
7" (Option)	368	227	224	8
7"	442	410	224	18

DD0002

单击下面可查看定价，库存，交付和生命周期等信息

[>>SGMICRO\(圣邦微电子\)](#)